



APMC 2025

2025 ASIA-PACIFIC MICROWAVE CONFERENCE

DEC 2 - 5, 2025 | ICC JEJU, Jeju Island, Korea

Session Title: [TB1] High Performance Power Amplifiers

Session Date: December 4 (Thu.), 2025

Session Time: 08:30-10:10

Session Room: Room B (Halla B)

[TB1-1]

08:30-08:50

An SL MBA with Enhanced Back-off Range Using a Novel Design Method for an Optimal Load-Modulation Profile

Tatsuya Itoh and Shinichi Tanaka (Shibaura Institute of Technology, Japan)

[TB1-2]

08:50-09:10

Sigmoid-Function-Based Variable Gain Amplifier for Dual-Input Power Amplifier

Wataru Yamamoto (Mitsubishi Electric Corporation, Japan); Takuma Torii (Mitsubishi Electric, Japan); Akihito Hirai (Mitsubishi Electric Corporation, Japan)

[TB1-3]

09:10-09:30

27dBm Output Power 2-Stage 5.9-7.12GHz PA for Wi-Fi Application in 130nm RF BiCMOS

Raphaël Paulin, Simon Bouvot, Jean-Christophe Mas, Cedric Durand and Daniel Gloria (STMicroelectronics, France)

[TB1-4]

09:30-09:50

Wideband High-Power Class EF2 Power Amplifier Based on Multiple Series Resonance

Sangyeop Kim (Sungkyunkwan University, Korea (South)); Sunwoo Nam (Samsung Electronics Company Ltd, Korea (South)); Yoonjung Lee, Seogyun Lim and Youngoo Yang (Sungkyunkwan University, Korea (South))

[TB1-5]

09:50-10:10

A Compact 40 dBm GaN/SiC MMIC Doherty Power Amplifier at FR3 Band for 6G Applications

Hossein Zaheri and Gregor Lasser (Chalmers University of Technology, Sweden)